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Telecommunication Gallium: The Future and Metal of Data Transmission

Antisar H. Albakoush
PhD., (Communication and IT, Technical college of civil aviation and meteorology, Libya)

***Abstract: All-optical signal process is taken into consideration as one of the promising answers to similarly enhance the data communication speed. Searching for a right material platform continues to be a crucial problem, which calls for numerous important residences which include excessive Kerr nonlinearity, negligible nonlinear loss, and capacity compatibility with the prevailing complementary metal-oxide semiconductor (CMOS) fabrication manner. In Recent years, many on-chip structures had been investigated, inclusive of silicon-on-insulator (SOI), Si3N4, silicon wealthy nitride (SRN), and amorphous silicon; However, those substances can hardly ever gain each excessive Kerr nonlinearity and occasional loss simultaneously. For instance, the SOI platform has the maximum mature fabrication generation and relatively excessive third-order optical nonlinearity, however its overall performance in Nonlinear photonics is usually confined via way of means of two-photon absorption (TPA) at a telecom wavelength of 1550 nm[-1]. Comparing with the above materials, aluminum gallium arsenide (AlxGa1-xAs) is turning into a promising candidate in incorporated nonlinear photonics with engineered band hole for TPA suppression, whilst preserving excessive third-order nonlinearity. By tuning the Al attention in AlxGa1-xAs, the TPA impact may be completely suppressed while the running photon strength is simply under its 1/2 of band hole. Moreover, the third-order optical nonlinear coefficient of AlxGa1-xAs is at the order of 10^{-17} m^2 W^{-1} , that is similar with Si and orders of value large than that of silicon nitride. Optical nonlinear results of AlxGa1-xAs waveguides at the insulator have already been significantly studied during the last few years which includes 2nd harmonic generation (SHG)[2], self-section modulation (SPM), cross-section modulation (XPM), and four-wave mixing (FWM).[3] In addition, the remarkable optical nonlinearity of AlGaAs waveguides has been carried out in programs which includes tremendous continuum generation (SCG)[4],three wavelength convertor, four Kerr frequency comb[5-7], or even excessive performance wavelength multicasting of pulse-amplitude modulation (PAM4) signals[8].
fiber-optic components fabricated on the same substrate as integrated circuits are important for future high-speed communications. One industry response has been the costly push to develop indium phosphide (InP) electronics. However, for fabrication simplicity, reliability and cost, gallium arsenide (GaAs) remains the established technology for integrated optoelectronics. This is an enabling technology for fibre-optic components that are lattice-matched to GaAs integrated circuits. We present experimental results showing significant internal optical power (24 mW) and speed (in terahertz) from GaAs optical emitters using deep-level transitions. Finally, we present theory showing the ultimate limit to the efficiency-bandwidth product of semiconductor deeplevel optical emitters[9].***
Keywords: kerr frequency comb, optical nonlinearity of AlGaAs, GaAs integrated circuits.

I. INTRODUCTION

Gallium is a metallic element that has unique properties that make it ideal for data transmission. It is non-toxic, non-flammable, and has a very low melting point. This makes it perfect for use in optical fiber and other data transmission technologies. In this paper, we will explore the potential of gallium as a data transmission medium, and why it may be the future of telecommunication.

A. Gallium Characteristics

Semi-insulating (SI) GaAs substrates are low-cost and have high-resistivity so can provide low-loss coplanar transmission-lines.

1) The electron mobility is high - six times higher than in silicon and almost 60% higher than In P. This enables low optical loss and high RF bandwidth in opto-electronic and electronic devices.
2) The band gap is comparatively large at 1.424eV. This yields the required characteristics of environmental stability, including a good degree of radiation hardness . Of the commonly-used semiconductors only diamond and GaN are higher. Silicon has a band gap of 1.12eV.
3) The related ternary AlxGa1-xAs is closely lattice-matched to GaAs throughout the range of aluminum fraction *x*. Increasing *x* further increases the band-gap and reduces the refractive-index. This enables considerable freedom in designing AlGaAs/GaAs hetero-structures for the confinement of electrons (in quantum wells) and photons (in optical waveguides)[10].

To fully exploit these properties, well qualified foundry processes have been developed over decades for the fabrication of GaAs discrete and monolithic microwave integrated circuits (MMICs). Thus, one further considerable benefit of GaAs for space applications is that it is already formally qualified to an appropriate standard for aerospace systems. GaAs has matured as semiconductor material to provide a viable IC technology.

II. MATERIAL AND METHODS

Compared with the set up silicon generation, the gain of GaAs appears to be most effective 1.5:1 for room temperature operation.[11] Silicon-on-sapphire generation may enhance the threat of silicon further, however clock frequencies past 2 GHz look like out of attain for S-O-S circuits with 1 µm-channel length. GaAs circuits could be advanced to S-O-S circuits even at clock frequencies properly underneath 2 GHz in VLSI, due to the fact GaAs gives decrease electricity dissipation at same speeds. GaAs is greater radiation-difficult than Si and is tolerant of wider temperature variations. It has been noted[12] that the velocity-electricity made of the loaded gate will increase for the numerous transistor kinds with inside the following: HEMT (three hundred K), GaAs EFET, Si-CMOS, Si-bipolar, GaAs DFET and Si-NMOS. On the alternative hand, the most gate number (for an assumed chip dissipation of 1-cm ~ area) which may be accommodated may be organized in descending order as Si-CMOS, Si-bipolar, 1HEMT (three hundred K), GaAs EFET, GaAs DFET and Si-NMOS. From the IC implementations, the subsequent conclusions can be derived from the frequencies and speeds received on the identical electricity levels: (i) The gain of GaAs, in particular HEMT is apparent for enforcing frequency dividers with low stage of complexity. (ii) In 4 x 4 bit multiplier IC, GaAs leads Si through an element of 2.5 due to MSI stage of complexity. The 8 × 8 bit multiplier has similar overall performance with both GaAs or Si. But in 16 × 16 bit configurations Si has an area over GaAs-primarily based totally circuits. There are evidences alternatively that GaAs-gadgets can out-carry out silicon gadgets with inside the shape of HEMT at 77 K. Until recently, it has now no longer been feasible to develop defect-flee GaAs wafers. Consequently GaAs gadgets were restrained in length and feature had terrible yields. If optical fiber structures are to development to excessive records rates, GaAs generation and circuit layout have to be advanced to gain the velocity and characteristic complexity required for multiplexing and regeneration of signals. The destiny prospect of GaAs IC is to combine excessive velocity common sense with optical sources (lasers and LED) and detectors for which Si isn't always suitable. Concerning the structure of Gbit/s circuits and sub-structures, serial processing, pipeline tactics and desirably cohesion fan-out systems like in systolic arrays must be preferred[13]. These architectural measures may in lots of instances require the improvement of recent most fulfilling signal-processing algorithms. Since the bottom fabric value is ten instances that of silicon, the gain has been very plenty with silicon. Much of the layout knowledge and software program strategies utilized in Si can also additionally show to be transferable to GaAs. These collectively with current advances in base fabric and processing can also additionally make GaAs greater competitive. GaAs on Si gives opportunities for understanding new styles of practical gadgets and IC with GaAs and Si gadgets.[14]

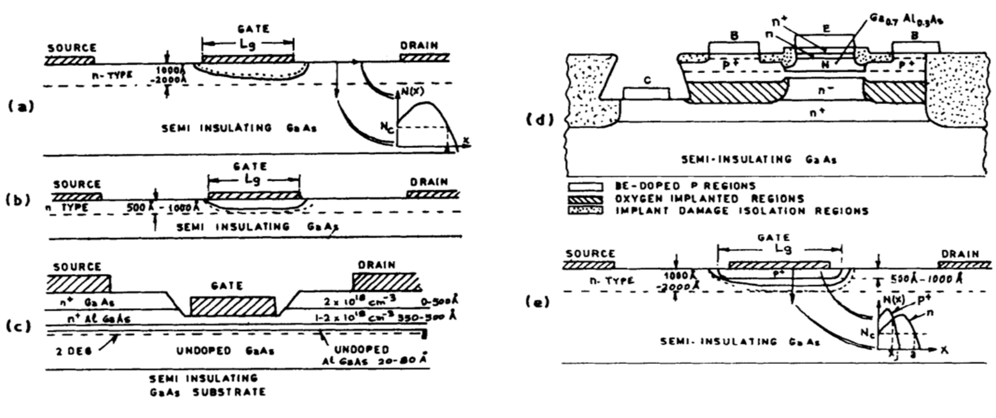
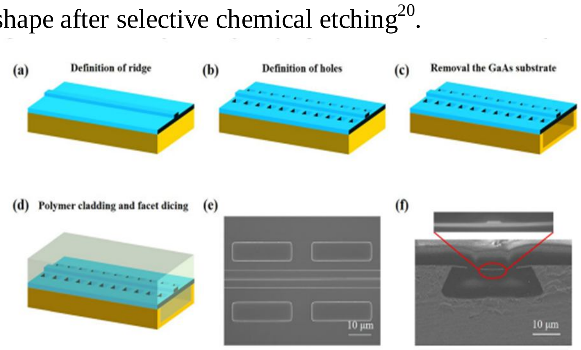


Figure 1. GaAs transistors. (a) Shows a depletion mode field effect transistor (DFET) with a threshold voltage of -0-7 V to -2.5 V, a high current capacity of0"l mA//~m, and high power dissipation of 0'25 mW/#m. (b) shows an enhancement mode field effect transistor (EFET) with a threshold voltage greater than 0 V, a low current capacity of 0"01 mA/Flm, low power dissipation of 0-01 roW/gin, and tight process controls of less than :t: 50 A,. (c) shows a high electron mobility transistor (HEMT), which is an enhancement and depletion device with a higher gate forward bias voltage of 0.7 to 0.9 V and high transconductance 450 mS/mm (300 K) to 520 mS/MM (77 K). (d) shows a heterojunction bipolar transistor (HBT) and (e) shows a junction field effect transistor (JFET) with large sidewall capacitance and tight process controls. Complementary devices are available[15]

Epitaxial grown at the GaAs substrate with inside the absence of wafer bonding. For this platform, numerous hundred nanometers thick AlGaAs film with an Al awareness of 0.18–0.2 is used because the center with inside the waveguide, at the same time as the epitaxial cladding layers are generally with the thickness of 2–4 lm. Both nanowire[16] or strip loaded[17], waveguides can be fabricated as section shifters and wavelength converters. However, rather low index assessment in such templates usually results in a huge powerful location and a small powerful index, which could significantly lessen the powerful nonlinear parameters. The opportunity answer is the AlGaAs-on-insulator platform, that's fabricated with the aid of using the use of the wafer bonding process. Several excessive-overall performance nonlinear devices had been formerly said inclusive of a low loss waveguide, a micro ring resonator (MRR) with excessive quality (Q) factor, and a soliton comb[17,18]. However, its programs are restrained with the aid of using the bonding yield and wafer length compatibility, specifically for huge location electro-optic integration.

In this paper, we shed light on recent studying about, the suspended AlGaAs ridge waveguide is designed and fabricated to aim for strong optical field confinement without bonding onto the SiO2 layer. Here, a 300-nm-thick Al0.5Ga0.5As film is directly epitaxial grown on the GaAs substrate using the molecular beam epitaxial (MBE) system At a temperature of 580 C. Figures 1(a)–1(d) display the fabrication method for the suspended AlGaAs waveguide. The AlGaAs ridge waveguides are patterned through the use of the usual e-beam lithography method through a JEOL6300 machine with AR-P 6200.09 resist. This sample is in the end transferred through inductively coupled plasma etching (ICP) in Oxford Plasma lab System 100. The waveguides are etched through Cl2 and BCl3 at a sluggish charge of four nm/s to exactly manipulate the etching depth. As proven in Fig. 1(b), holes for the suspension method are positioned on each facets of the AlGaAs ridge waveguide, that are patterned the use of direct laser writing through a DWL 66þ system and accompanied through ICP etching with a comparable recipe. The pinnacle view scanning electron microscope (SEM) photo of this shape after AlGaAs ICP etching is proven in Fig. 1(e). The residual photoresist is wiped clean through dipped in acetone dipping and oxygen plasmas through a reactive ion etching (RIE) machine. To obtain the suspended shape whilst ensuring sturdy optical confinement inside the AlGaAs waveguide (n¼ 3.18), the GaAs (n¼ 3.43) below the ridge waveguide is eliminated through selective moist etching. Citric acid monohydrate is first blended 1:1 with DI water at room temperature[19]. Considering the etching charge and selectivity among GaAs and Al0.5Ga0.5As, an optimized citric acid/H2O2 answer with the ratio of 6:1 is used, and the measured etching charge for GaAs is a 160 nm/min at room temperature. Figure 1(c) indicates the suspended waveguide shape after selective chemical etching[20].



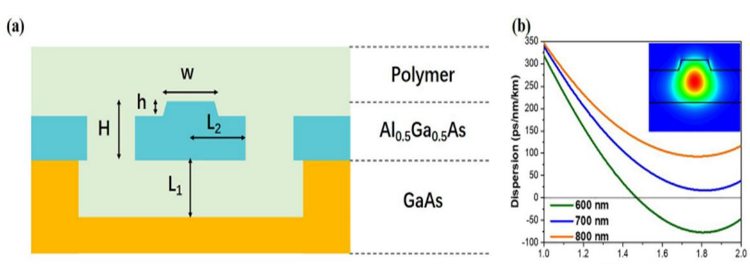


FIG. 3. (a) Cross-sectional geometries and material compositions of the suspended AlGaAs waveguide. H ¼ 300 nm, h ¼ 70 nm, w ¼ 700 nm, L1 ¼ 6.1 lm, and L2 ¼ 5 lm. (c) Calculated waveguide dispersion for the TE mode in different waveguide widths. Inset: electric field distribution of the TE mode for a 700 nm-width waveguide[21].

$$\mathbf{A}_{eff} = \frac{\left[\int_{-\infty}^{+\infty} E(x,y)^2 dxdy\ \right]^2}{\int_{-\infty}^{+\infty} E(x,y)^4 dxdy}$$

Fig. 3(a) indicates the cross-sectional geometries for the AlGaAs suspended waveguide, the ridge width (w) is designed to be seven hundred nm, and the ridge height (h) is 70 nm. The simulated mode profile of the transverse electric (TE) mode is proven with inside the inset photograph of Fig. 3(b). The powerful mode area (Aeff) is calculated to be 0.415 lm2 , decided via way of means of the subsequent equation: wherein E (x,y) is the electrical discipline intensity[22]. To take away the scattering loss brought about via way of means of wet-etching holes, the gap among the hollow area and the middle of ridge (L2) is designed to be five lm. The mode leakage as a result of the optical evanescent coupling from the AlGaAs waveguide to the GaAs substrate also can be neglected, because the measured gap (L1) is over 6 lm. Figure 3(b) indicates the calculated dispersion consequences for the AlGaAs waveguide with diverse ridge widths. It may be visible that the dispersion is 53 ps /nm km for the 700nm-width waveguide on the wavelength of 1550 nm. In order to analyze the nonlinear residences of suspended AlGaAs waveguides, the transmission spectrum of a pulse laser with the width of 1.5 ps positioned at 1552 nm turned into measured. The enter mild is showed to be on the TE mode via way of means of the usage of a polarization controller, coupled into and out of the waveguide thru lens fibers and inversed tapers. The transmission spectra are measured via way of means of the usage of an optical spectrum analyzer (OSA)[23].

The nonlinear overall performance of suspended AlGaAs waveguides may be advanced through lowering the coupling and propagation loss thru fabrication optimization, specially the sturdy loss triggered from waveguide deformation may be avoided. We consider that the suspended AlGaAs waveguide can also additionally promise brilliant ability in knowing high performance on-chip nonlinear optical sign processing[24].

III. CONCLUSION

The digital age has driven the need for faster and more reliable data transmission. As the demand for data grows, so does the need for faster and more efficient ways to transmit it.

The AlGaAs material system is versatile, permitting designs to be realized for a wide range of optical wavelengths. We have presented basic design data to demonstrate the potential for significant advantage in terms of drive-power at shorter wavelengths[25]. Gallium is a semiconductor, which means it can be used to create faster and more efficient data transmission. Gallium can also be used to create smaller and more compact data transmitters. This is because gallium can be condensed into a liquid state, which reduces its size and weight.

Gallium is a metallic element that has unique properties that make it ideal for data transmission. It is non-toxic, non-flammable, and has a very low melting point. This makes it perfect for use in optical fiber and other data transmission technologies. The benefits of gallium are clear. It has the potential to make data transmission faster, more efficient, and more compact. In the future, gallium may become the standard for data transmission.

The quest for logic devices that can operate at even higher frequencies and can be packed more densely in an IC package is a continuing process. Designers have high hopes for other new technologies, such as integrated injection logic (I2 L), silicon-onsapphire (SOS), gallium arsenide (GaAs), and Josephson junction circuits. Eventually, propagation delays will be measured in picoseconds, and circuit densities will enable the supercomputer of today to become the desktop computer of tomorrow[26].

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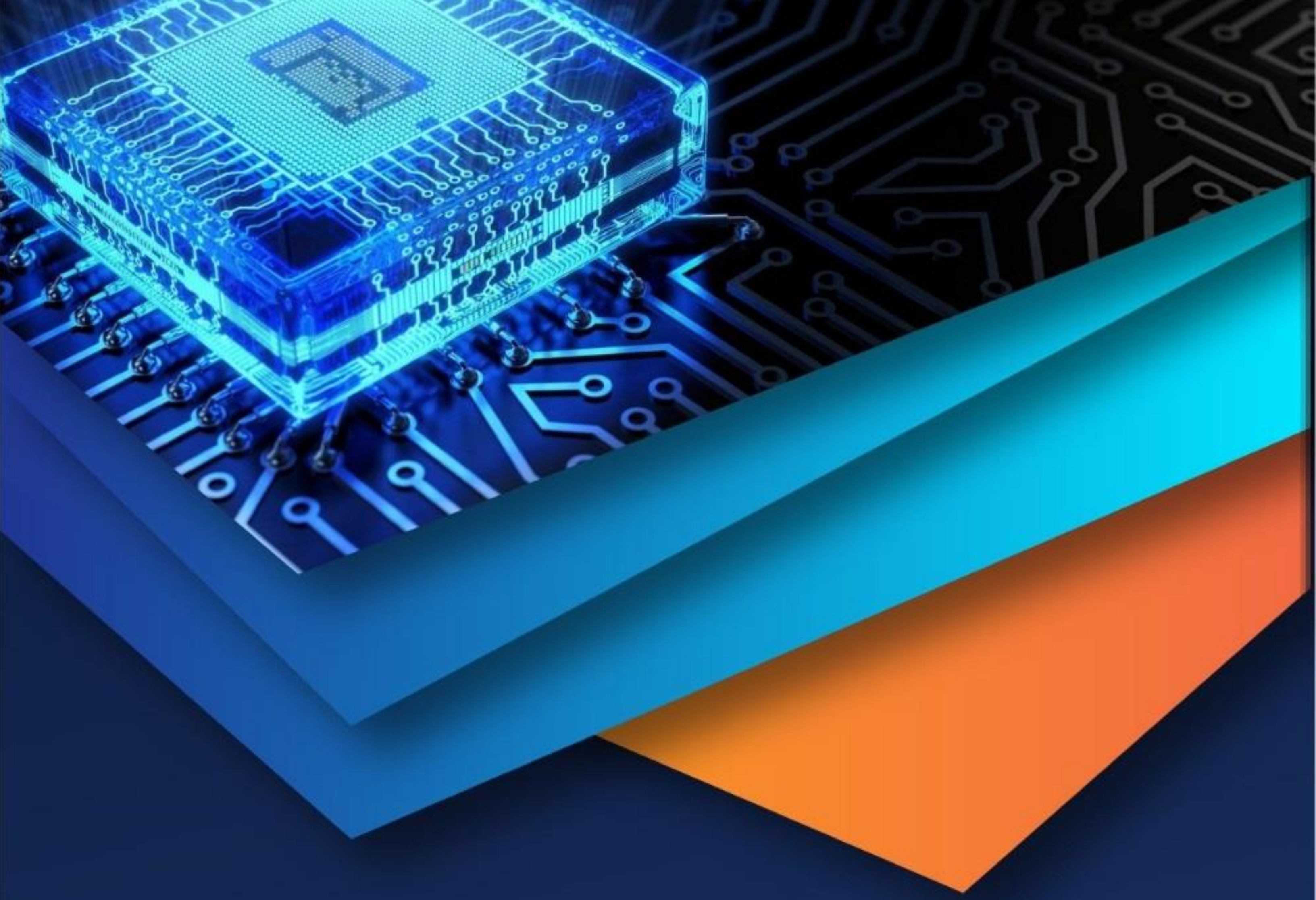

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